

NPN Silicon RF power transistor

MRF464

Description:

MRF464 is designed primarily for applications as a high-power linear amplifier from 2.0 to 30 MHz, in single sideband mobile, marine and base station equipment.

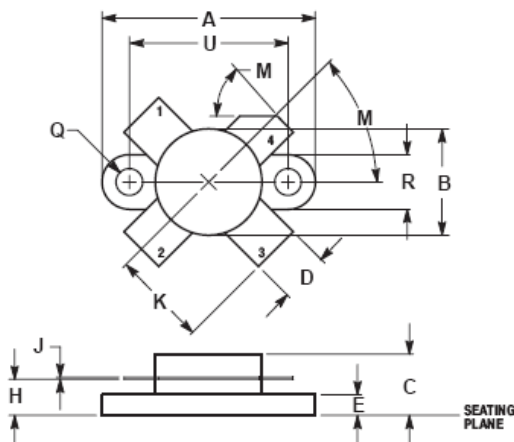
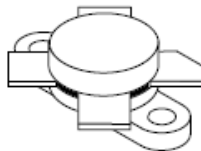
Features:

Specified 28 Volt, 30 MHz Characteristics:
Output Power = 80 W (PEP), Minimum Gain = 15 Db, Efficiency = 40%
Intermodulation Distortion = -32 dB (Max).

Maximum Ratings:

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CBO}	65	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	10	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	250 1.4	Watts $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

Drawings:



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.960	0.990	24.39	25.14
B	0.465	0.510	11.82	12.95
C	0.229	0.275	5.82	6.98
D	0.216	0.235	5.49	5.96
E	0.084	0.110	2.14	2.79
H	0.144	0.178	3.66	4.52
J	0.003	0.007	0.08	0.17
K	0.435	---	11.05	---
M	45°NOM		45°NOM	
Q	0.115	0.130	2.93	3.30
R	0.246	0.255	6.25	6.47
U	0.720	0.730	18.29	18.54

STYLE 1:
PIN 1: EMITTER
2: BASE
3: EMITTER
4: COLLECTOR

CASE211-11/SOT121